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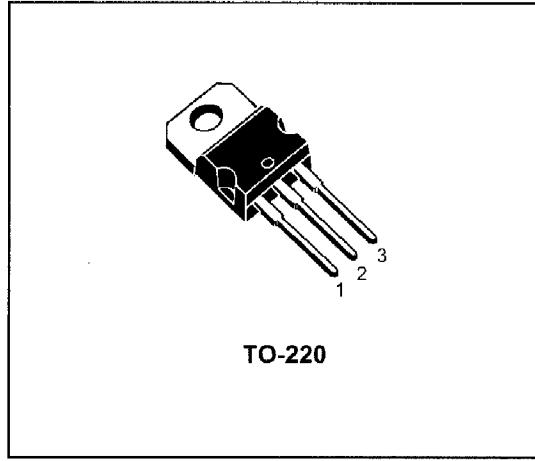
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BUZ11

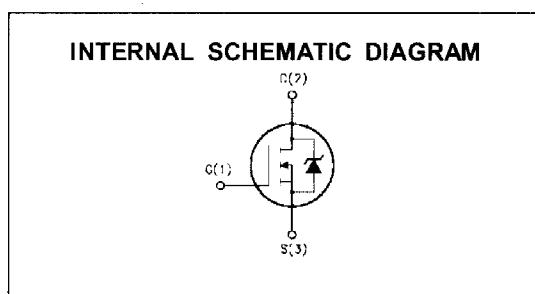
N - CHANNEL 50V - 0.03Ω - 33A TO-220 STripFET™ MOSFET

TYPE	V _{DSS}	R _{D(on)}	I _D
BUZ11	50 V	< 0.04 Ω	33 A

- TYPICAL R_{D(on)} = 0.03 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE



TO-220

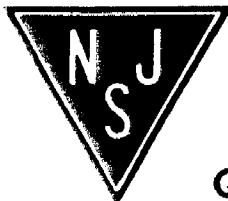


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	50	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	50	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	33	A
I _{DM}	Drain Current (pulsed)	134	A
P _{tot}	Total Dissipation at T _c = 25 °C	90	W
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C
	DIN HUMIDITY CATEGORY (DIN 40040)	E	
	IEC CLIMATIC CATEGORY (DIN IEC 68-1)	55/150/56	

First digit of the datecode being Z or K identifies silicon characterized in this datasheet.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



BUZ11

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.67	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^{\circ}\text{C}/\text{W}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	33	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 25\text{ V}$)	200	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ $V_{GS} = 0$	50			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_j = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 1\text{ mA}$	2.1	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{V}$ $I_D = 19\text{ A}$		0.03	0.04	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} = 15\text{ V}$ $I_D = 19\text{ A}$	10	17		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0$		2100 260 65		pF pF pF

SWITCHING

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 18\text{ A}$		40 200		ns ns
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$R_{GS} = 50\text{ }\Omega$ $V_{GS} = 10\text{ V}$		220 110		ns ns

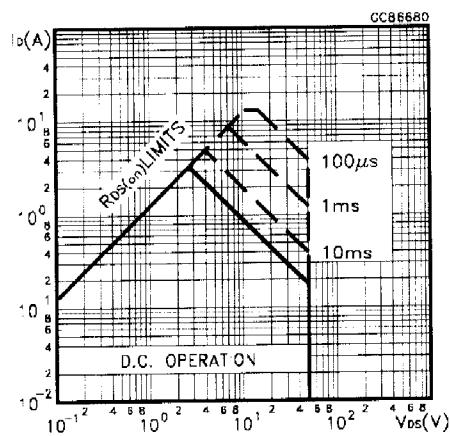
ELECTRICAL CHARACTERISTICS (continued)

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{SD}	Source-drain Current				33	A
I _{SDM}	Source-drain Current (pulsed)				134	A
V _{SD} (*)	Forward On Voltage	I _{SD} = 60 A V _{GS} = 0			1.8	V
t _{rr}	Reverse Recovery Time	I _{SD} = 36 A di/dt = 100 A/μs V _{DD} = 30 V T _j = 150 °C		75		ns
Q _{rr}	Reverse Recovery Charge			0.24		μC

(*) Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area



Thermal Impedance

